Silicon P-Channel MOS FET

HITACHI

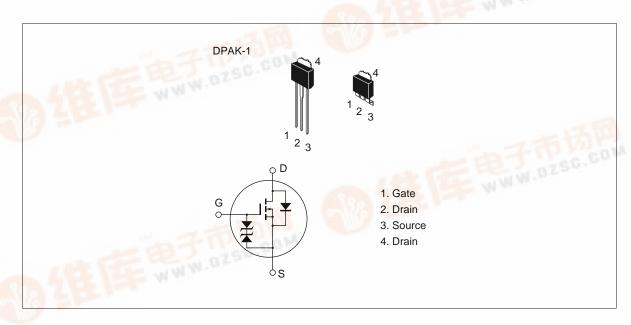
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline





Absolute Maximum Ratings (Ta = 25°C)

| Item | Symbol | Ratings | Unit | |
|---|------------------------------|-------------|------|--|
| Drain to source voltage | $V_{\scriptscriptstyle DSS}$ | -600 | V | |
| Gate to source voltage | $V_{\sf GSS}$ | ±15 | V | |
| Drain current | I _D | -0.5 | Α | |
| Drain peak current | I _{D(pulse)} *1 | -1.0 | A | |
| Body to drain diode reverse drain current | I _{DR} | -0.5 | Α | |
| Channel dissipation | Pch*2 | 20 | W | |
| Channel temperature | Tch | 150 | °C | |
| Storage temperature | Tstg | -55 to +150 | °C | |

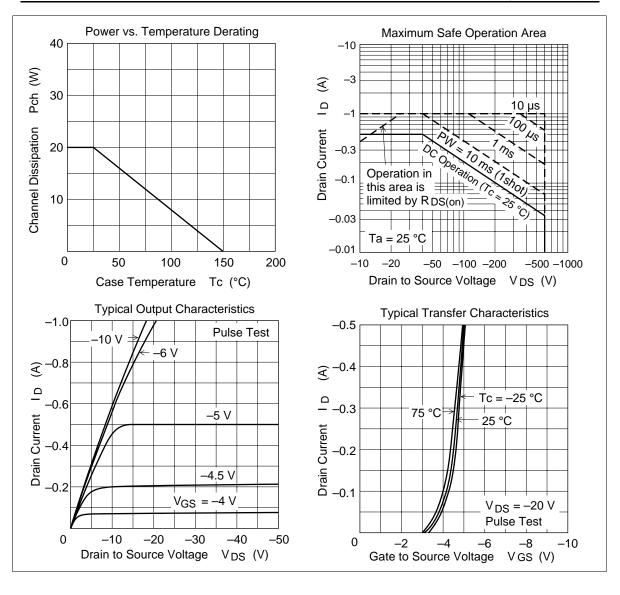
Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

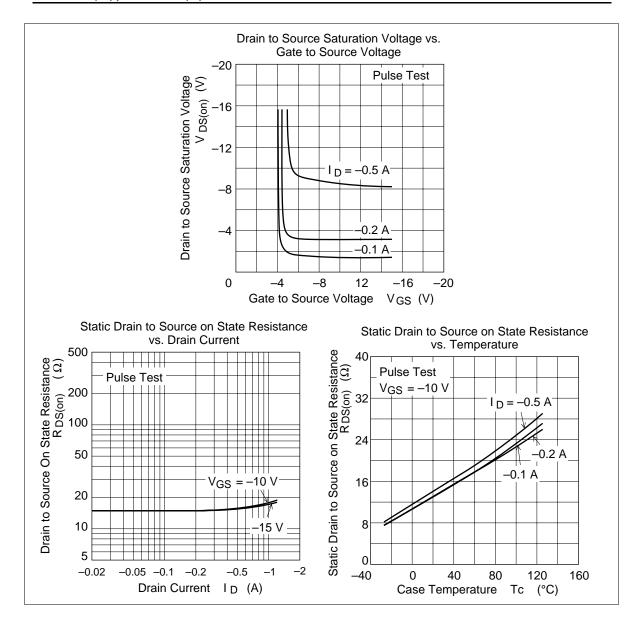
2. Value at $T_c = 25^{\circ}C$

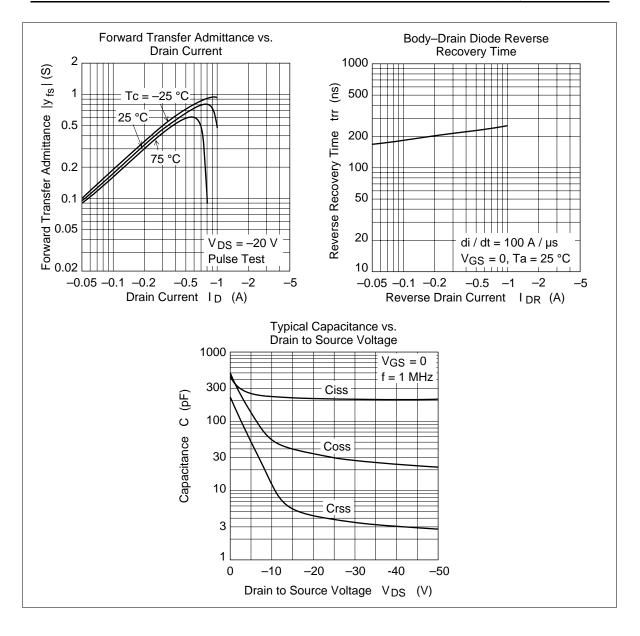
Electrical Characteristics ($Ta = 25^{\circ}C$)

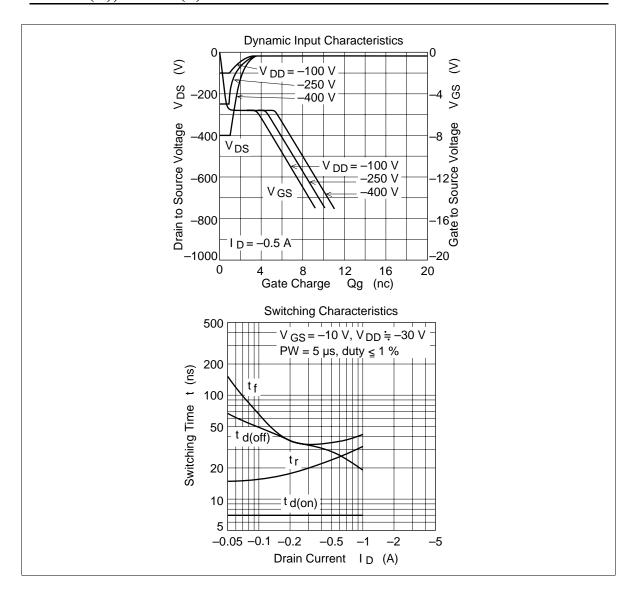
| Item | Symbol | Min | Тур | Max | Unit | Test conditions |
|--|----------------------|------|-------|------|------|---|
| Drain to source breakdown voltage | $V_{(BR)DSS}$ | -600 | _ | _ | V | $I_{D} = -10 \text{ mA}, V_{GS} = 0$ |
| Gate to source breakdown voltage | $V_{(BR)GSS}$ | ±15 | _ | _ | V | $I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$ |
| Gate to source leak current | I _{GSS} | _ | _ | ±10 | μΑ | $V_{GS} = \pm 12 \text{ V}, V_{DS} = 0$ |
| Zero gate voltage drain current | I _{DSS} | _ | _ | -100 | μΑ | $V_{DS} = -500 \text{ V}, V_{GS} = 0$ |
| Gate to source cutoff voltage | $V_{\text{GS(off)}}$ | -2.0 | _ | -4.0 | V | $I_{D} = -1 \text{ mA}, V_{DS} = -10 \text{ V}$ |
| Static drain to source on state resistance | R _{DS(on)} | _ | 15 | 25 | Ω | $I_D = -0.3 \text{ A}, V_{GS} = -10 \text{ V}^{*1}$ |
| Forward transfer admittance | y _{fs} | 0.3 | 0.45 | _ | S | $I_D = -0.3 \text{ A}, V_{DS} = -20 \text{ V}^{*1}$ |
| Input capacitance | Ciss | _ | 220 | _ | pF | $V_{DS} = -10 \text{ V}, V_{GS} = 0,$ |
| Output capacitance | Coss | _ | 55 | _ | pF | f = 1 MHz |
| Reverse transfer capacitance | Crss | _ | 13 | _ | pF | |
| Turn-on delay time | $t_{d(on)}$ | _ | 7 | _ | ns | $I_D = -0.3 \text{ A}, V_{GS} = -10 \text{ V},$ |
| Rise time | t _r | _ | 20 | _ | ns | $R_L = 100 \Omega$ |
| Turn-off delay time | t _{d(off)} | _ | 35 | _ | ns | |
| Fall time | t _f | _ | 35 | _ | ns | |
| Body to drain diode forward voltage | V_{DF} | _ | -0.85 | _ | V | $I_F = -0.5 \text{ A}, V_{GS} = 0$ |
| Body to drain diode reverse recovery time | t _{rr} | _ | 230 | _ | ns | $I_F = -0.5 \text{ A}, V_{GS} = 0,$ $di_F/dt = 50 \text{ A}/\mu\text{s}$ |
| Note: 1 Dules test | | | | | | |

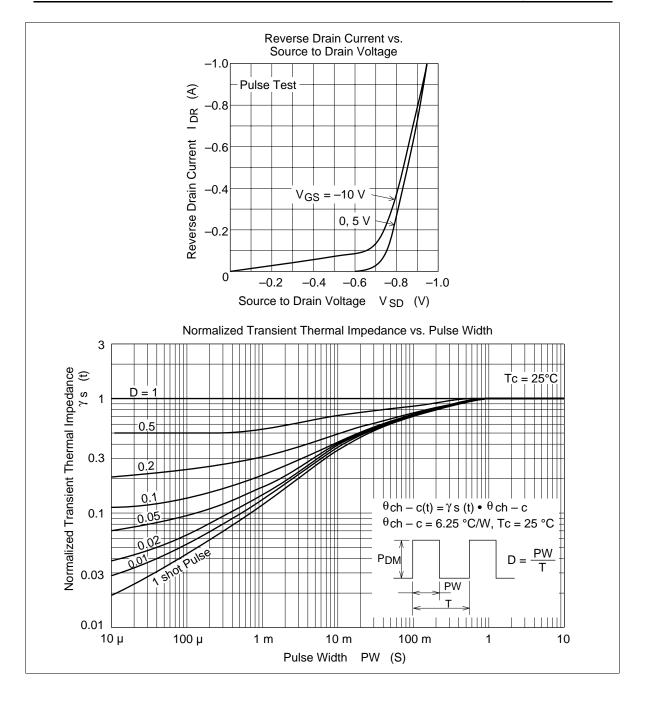
Note: 1. Pulse test

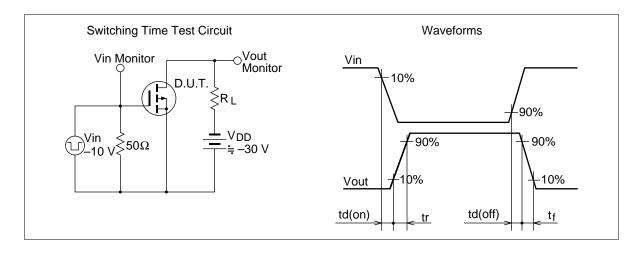


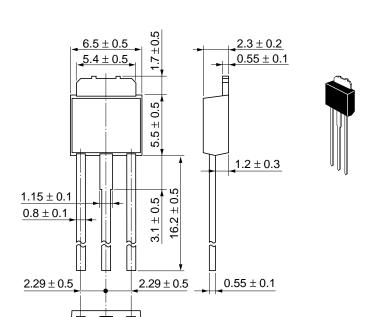












Unit: mm

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